

Pei-Cheng Ku

List of Publications by Year in descending order

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50
papers

1,685
citations

567281

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all docs

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docs citations

50
times ranked

1845
citing authors

#	ARTICLE	IF	CITATIONS
1	Ultrathin Optics-Free Spectrometer with Monolithically Integrated LED Excitation. <i>Micromachines</i> , 2022, 13, 382.	2.9	1
2	Optically Controlled Spin Gate Using GaN Quantum Dots. <i>ACS Photonics</i> , 2022, 9, 1529-1534.	6.6	5
3	Low-Profile Shear Force Tactile Sensor Based on Optical Methods. <i>IEEE Electron Device Letters</i> , 2022, 43, 1081-1084.	3.9	4
4	Ultracompact Optics-Free Chip-Scale Spectrometer with Integrated LEDs. , 2021, , .		0
5	Toward Artificial Fingertips Based on GaN Optical Tactile Sensors. , 2021, , .		0
6	Mapping tensorial shear stress with light-emitting GaN nanopillars. , 2021, , .		1
7	Two-photon controlled-phase gates enabled by photonic dimers. <i>Physical Review A</i> , 2021, 103, .	2.5	8
8	Designing an Ultrathin Film Spectrometer Based on III-Nitride Light-Absorbing Nanostructures. <i>Micromachines</i> , 2021, 12, 760.	2.9	5
9	Ultrathin Tactile Sensors with Directional Sensitivity and a High Spatial Resolution. <i>Nano Letters</i> , 2021, 21, 8304-8310.	9.1	10
10	Proposal for chip-scale generation and verification of photonic dimers. <i>Applied Physics Letters</i> , 2021, 119, 224001.	3.3	0
11	Wavelength tuning in the purple wavelengths using strain-controlled Al _x Ga _{1-x} N/GaN disk-in-wire structures. <i>Applied Physics Letters</i> , 2020, 116, 041102.	3.3	6
12	On-chip optical spectrometer based on GaN wavelength-selective nanostructural absorbers. <i>Applied Physics Letters</i> , 2020, 116, 081103.	3.3	15
13	An Empirical Model for GaN Light Emitters with Dot-in-Wire Polar Nanostructures. <i>Micromachines</i> , 2020, 11, 82.	2.9	2
14	Variable transmission optical filter based on an actuated origami structure. <i>Applied Optics</i> , 2020, 59, 2963.	1.8	1
15	Toward scalable III-nitride quantum dot structures for quantum photonics. <i>Semiconductors and Semimetals</i> , 2020, , 1-27.	0.7	0
16	Design Chip-Scale Integration of Tunable Short-Wavelength Photonic Devices. , 2020, , .		0
17	(Invited) GaN Optoelectronic Devices Based on Local Strain Engineering. <i>ECS Transactions</i> , 2020, 98, 415-422.	0.5	0
18	(Invited) GaN Optoelectronic Devices Based on Local Strain Engineering. <i>ECS Meeting Abstracts</i> , 2020, MA2020-02, 1740-1740.	0.0	0

#	ARTICLE	IF	CITATIONS
19	A tensorial shear stress sensor based on light-emitting GaN nanopillars. Applied Physics Letters, 2019, 115, .	3.3	7
20	Mechanisms of inhomogeneous broadening in InGaN dot-in-wire structures. Journal of Applied Physics, 2019, 126, 083104.	2.5	6
21	Feasibility study of nanopillar LED array for color-tunable lighting and beyond. Optics Express, 2019, 27, 38229.	3.4	4
22	Transparent Displays Using Strain-Engineered Nanopillar Light-Emitting Diodes. , 2019, , .		0
23	Integrated parabolic nanolenses on MicroLED color pixels. Nanotechnology, 2018, 29, 165201.	2.6	7
24	Strain Effects in Gallium Nitride Adsorption on Defective and Doped Graphene: First-Principles Calculations. Crystals, 2018, 8, 58.	2.2	8
25	Wavelength tunable InGaN/GaN nano-ring LEDs via nano-sphere lithography. Scientific Reports, 2017, 7, 42962.	3.3	34
26	LED Lights With Hidden Intensity-Modulated Blue Channels Aiming for Enhanced Subconscious Visual Responses. IEEE Photonics Journal, 2017, 9, 1-9.	2.0	3
27	Monolithic integration of individually addressable light-emitting diode color pixels. Applied Physics Letters, 2017, 110, 111103.	3.3	50
28	Impact of carrier localization on recombination in InGaN quantum wells and the efficiency of nitride light-emitting diodes: Insights from theory and numerical simulations. Applied Physics Letters, 2017, 111, .	3.3	62
29	Color mixing from monolithically integrated InGaN-based light-emitting diodes by local strain engineering. Applied Physics Letters, 2017, 111, .	3.3	34
30	III-Nitride Semiconductor Single Photon Sources. Series in Optics and Optoelectronics, 2017, , 661-669.	0.0	0
31	Strain-induced red-green-blue wavelength tuning in InGaN quantum wells. Applied Physics Letters, 2016, 108, 071104.	3.3	36
32	Site-controlled InGaN/GaN single-photon-emitting diode. Applied Physics Letters, 2016, 108, .	3.3	24
33	Charge-tunable indium gallium nitride quantum dots. Physical Review B, 2016, 93, .	3.2	11
34	Elliptical quantum dots as on-demand single photons sources with deterministic polarization states. Applied Physics Letters, 2015, 107, .	3.3	33
35	Plasmonic Enhancement of Single Photon Emission from a Site-Controlled Quantum Dot. ACS Photonics, 2015, 2, 1065-1070.	6.6	22
36	GaN Micromechanical Resonators with Meshed Metal Bottom Electrode. Materials, 2015, 8, 1204-1212.	2.9	5

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37	Monolithically Integrated $\lambda/4$ LEDs on Silicon Neural Probes for High-Resolution Optogenetic Studies in Behaving Animals. <i>Neuron</i> , 2015, 88, 1136-1148.	8.1	372
38	Carrier dynamics in site- and structure-controlled InGaN/GaN quantum dots. <i>Physical Review B</i> , 2014, 90, .	3.2	23
39	How much better are InGaN/GaN nanodisks than quantum wellsâ€”Oscillator strength enhancement and changes in optical properties. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	32
40	Single photon emission from site-controlled InGaN/GaN quantum dots. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	44
41	Site-controlled single photon emitters based on InGaN/GaN quantum dots. , 2012, , .		0
42	Fabrication of nanoscale zero-mode waveguides using microlithography for single molecule sensing. <i>Nanotechnology</i> , 2012, 23, 455301.	2.6	6
43	The metal-clad semiconductor nanoring laser and its scaling properties. <i>Optics Express</i> , 2011, 19, 3218.	3.4	11
44	Subwavelength Surface Plasmon Optical Cavityâ€™Scaling, Amplification, and Coherence. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2009, 15, 1521-1528.	2.9	11
45	Slow Light Using P-Doped Semiconductor Heterostructures for High-Bandwidth Nonlinear Signal Processing. <i>Journal of Lightwave Technology</i> , 2008, 26, 3811-3817.	4.6	12
46	Slow-light optical buffers: capabilities and fundamental limitations. <i>Journal of Lightwave Technology</i> , 2005, 23, 4046-4066.	4.6	438
47	Slow light in semiconductor quantum wells. <i>Optics Letters</i> , 2004, 29, 2291.	3.3	291
48	Thermal oxidation of AlGaAs: modeling and process control. <i>IEEE Journal of Quantum Electronics</i> , 2003, 39, 577-585.	1.9	15
49	Buried selectively-oxidized AlGaAs structures grown on nonplanar substrates. <i>Optics Express</i> , 2002, 10, 1003.	3.4	10
50	Analysis of stability in two-mode laser systems. <i>IEEE Journal of Quantum Electronics</i> , 1996, 32, 1377-1382.	1.9	16